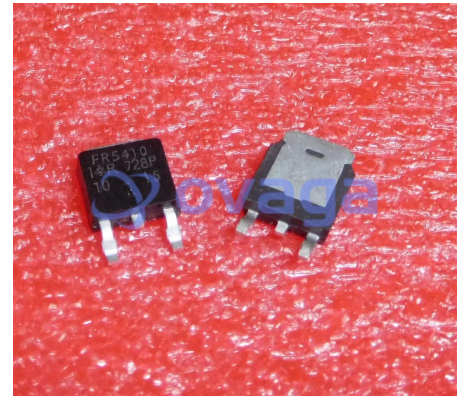


MOSFET, Power; P-Ch; VDSS -100V; RDS(ON) 0.205Ω; ID -13A; D-Pak (TO-252AA); PD 66W

Manufacturers	Infineon Technologies Corporation
Package/Case	TO-252
Product Type	Transistors
RoHS	Green
Lifecycle	



Images are for reference only

Please submit RFQ for IRFR5410PBF or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

- Ultra Low On-Resistance
- P-Channel
- Surface Mount (IRFR5410)
- Straight Lead (IRFU5410)
- Advanced Process Technology
- Fast Switching
- Fully Avalanche Rated

Features

RoHS Compliant

Low RDS(on)

Industry-leading quality

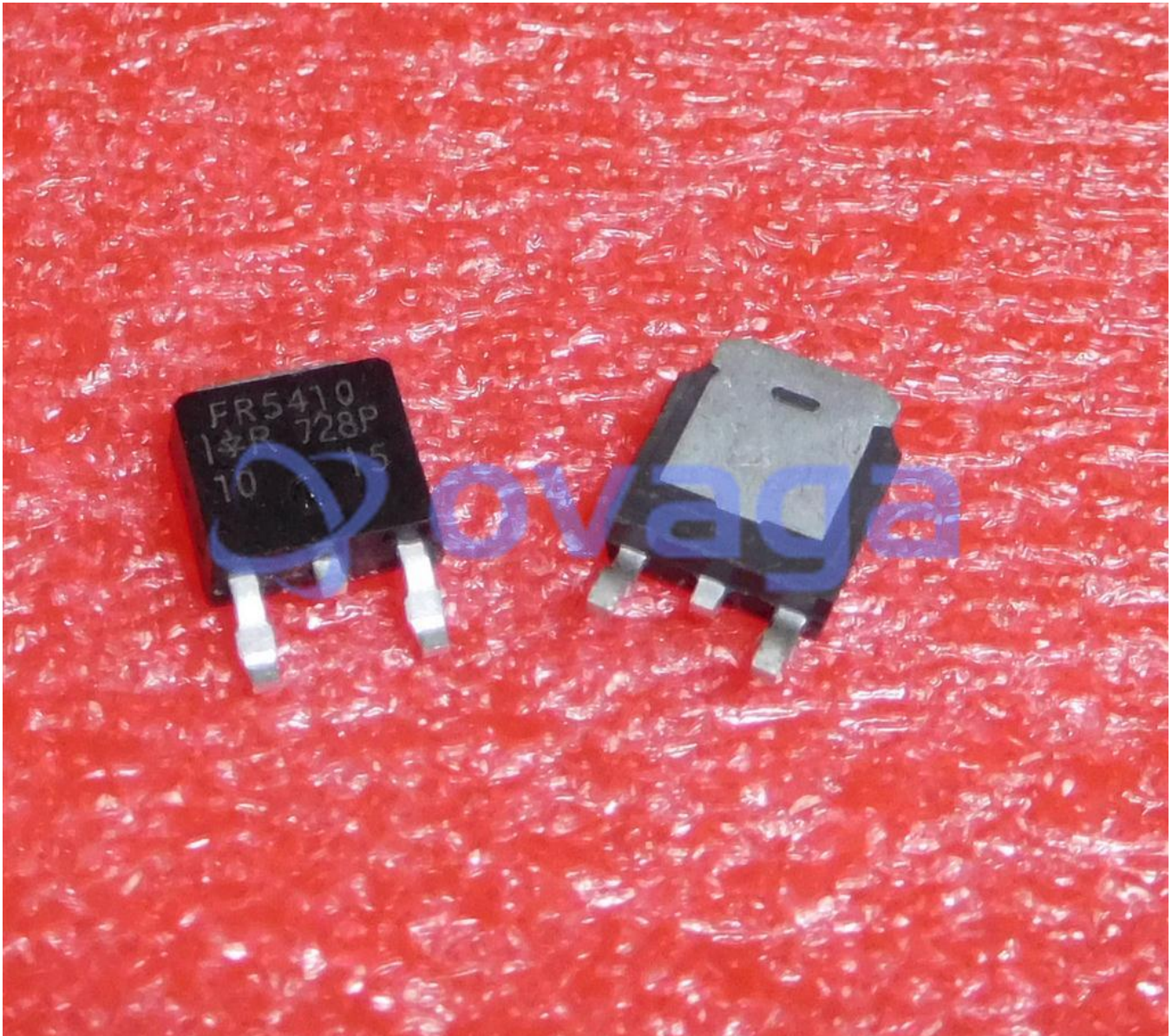
Dynamic dv/dt Rating

Fast Switching

Fully Avalanche Rated

175°C Operating Temperature

P-Channel MOSFET

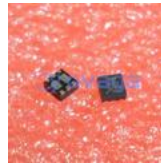


Related Products



[IRLTS6342TRPBF](#)

Infineon Technologies Corporation
TSOP-6



[IRLHS6376TRPBF](#)

Infineon Technologies Corporation
PQFN2x2DD



[IRF9310PBF](#)

Infineon Technologies Corporation
SOIC-8



[IRFH9310TRPBF](#)

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PQFN-8



[IRF9358TRPBF](#)

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SOP-8



[IRFB7430PBF](#)

Infineon Technologies Corporation
TO-220



[IRFB3307ZPBF](#)

Infineon Technologies Corporation
TO-220AB



[IRF7351TRPBF](#)

Infineon Technologies Corporation
SOIC-8